



SSCPA94GS6

PNP High-voltage Transistor

➤ Features

VCB	VCE	VEB	IC
-400V	-400V	-5V	-200mA

➤ Description

This device is designed for general-purpose high-voltage amplifiers and gas discharge display drivers. It is Ideal for medium power amplification and switching.

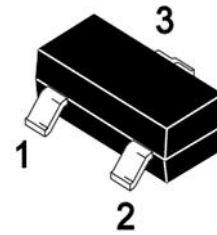
➤ Applications

- Telephony
- Professional communication equipment

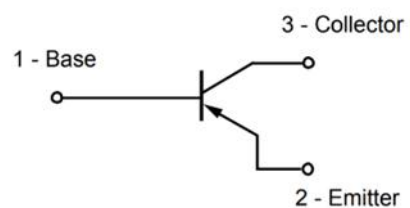
➤ Ordering Information

Device	Package	Shipping
SSCPA94GS6	SOT-23	3000/Reel

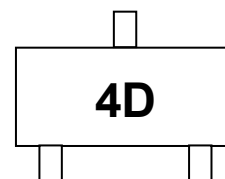
➤ Pin configuration



SOT-23



Circuit Diagram



Marking (Top View)

➤ **Absolute Maximum Ratings($T_A=25^{\circ}\text{C}$ unless otherwise noted)**

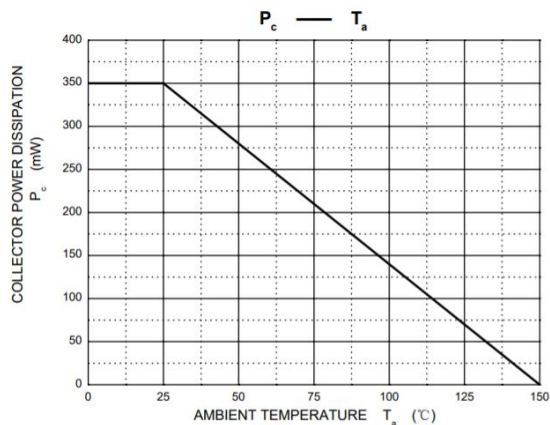
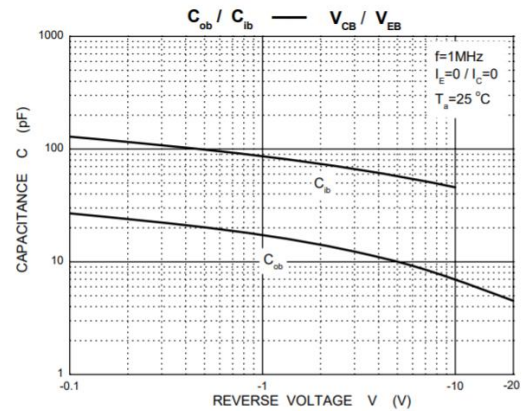
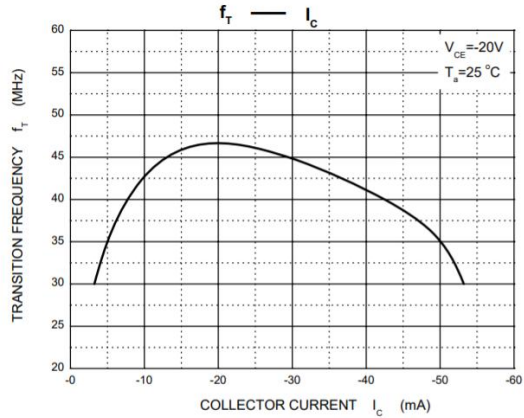
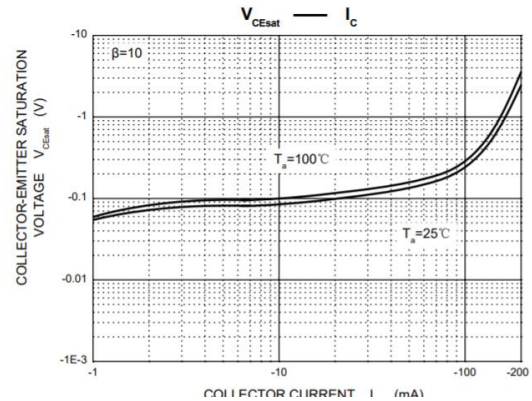
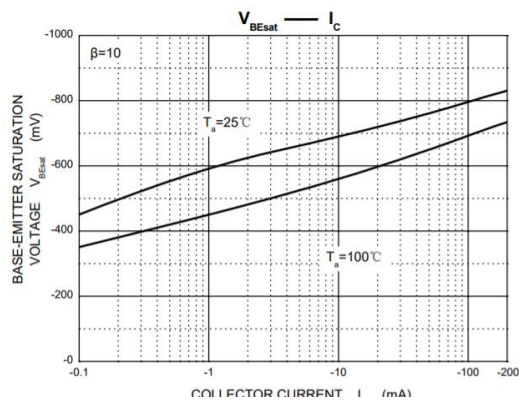
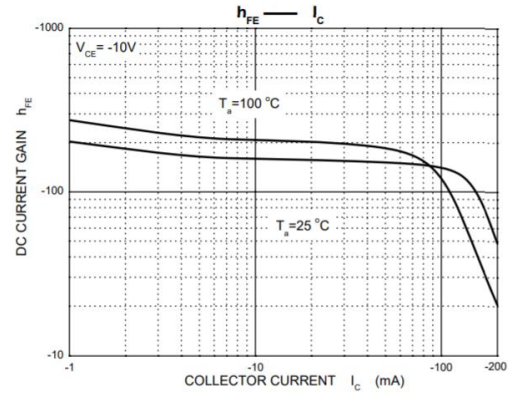
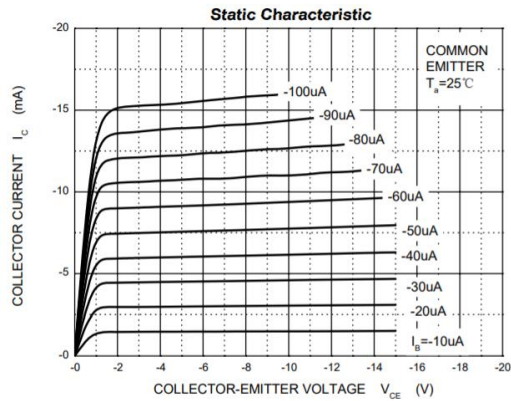
Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-400	V
Collector- Emitter Voltage	V_{CEO}	-400	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current-Continuous	I_C	-200	mA
Collector Current-Pulsed	I_{CM}	-300	mA
Collector Power Dissipation	P_C	350	mW
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	357	$^{\circ}\text{C/W}$
Junction Temperature	T_J	-55 to 150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55 to 150	$^{\circ}\text{C}$

➤ **Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)**

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C=-100\mu\text{A}$, $I_E=0$	-400			V
Collector-emitter Breakdown Voltage	BV_{CEO}	$I_C=-1\text{mA}$, $I_B=0$	-400			V
Emitter -Base Breakdown Voltage	BV_{EBO}	$I_E=-100\mu\text{A}$, $I_C=0$	-5			V
Collector Cutoff Current	I_{CBO}	$V_{CB}=-400\text{V}$, $I_E=0$			-0.1	μA
Collector Cutoff Current	I_{CEO}	$V_{CB}=-400\text{V}$, $I_E=0$			-5	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=-4\text{V}$, $I_C=0$			-0.1	μA
DC Current Gain	h_{FE1}	$V_{CE}=-10\text{V}$, $I_C=-10\text{mA}$	80			
	h_{FE2}	$V_{CE}=-10\text{V}$, $I_C=-1\text{mA}$	70			
	h_{FE3}	$V_{CE}=-10\text{V}$, $I_C=-100\text{mA}$	40			
	h_{FE4}	$V_{CE}=-10\text{V}$, $I_C=-50\text{mA}$	40			
Collector-Emitter Saturation Voltage	$V_{CE(sat)1}$	$I_C=-50\text{mA}$, $I_B=-1\text{mA}$			-0.2	V
	$V_{CE(sat)2}$	$I_C=-10\text{mA}$, $I_B=-5\text{mA}$			-0.3	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=-10\text{mA}$, $I_B=-1\text{mA}$			-0.75	V
Transition frequency	f_T	$V_{CE}=-20\text{V}$, $I_C=-10\text{mA}$ $f=30\text{MHz}$	50			MHz

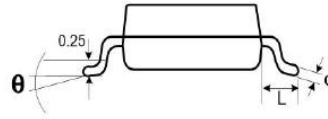
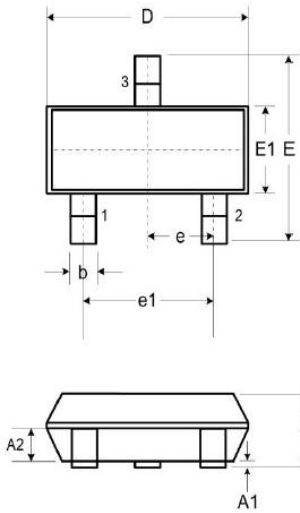


➤ Typical Performance Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)



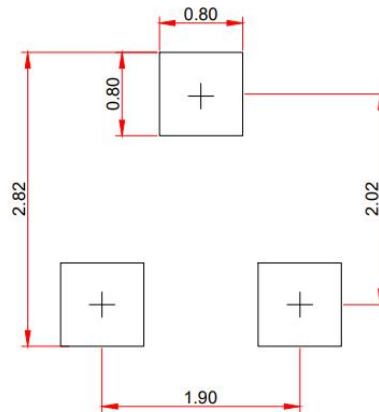


➤ Package Information



DIM	Millimeters		
	Min.	Typ.	Max.
A	0.89	-	1.12
A1	0.01	-	0.10
A2	0.88	0.95	1.02
b	0.30	-	0.51
c	0.08	-	0.18
D	2.80	2.90	3.04
E	2.10	2.37	2.64
E1	1.20	1.30	1.40
e	0.95		
e1	1.90		
L	0.40	0.50	0.60
L1	0.55		
N	3		
θ	0°	-	8°

Recommended Pad outline (Unit: mm)





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